



POWER DISCRETES & MODULES

- ▶ Voltage & Current Regulation Diodes
- ▶ Small Signal Diodes and Diode Arrays
- ▶ IGBT
- ▶ Power MOSFET
- ▶ Silicon Carbide (SiC) Semiconductor
- ▶ Power Modules
- ▶ JFET
- ▶ BJT (BiPolar Junction Transistor)
 - BJT Modules (Power Integrated Circuit, PIC)
 - Darlington Transistors
 - Darlington Transistor Array
 - NPN PNP Complimentary Transistor
 - **NPN Transistor**
 - PNP Transistor
- ▶ Legacy Power Discretets & Modules
- ▶ Diode and Rectifier Devices

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JAN2N1481 (#52526)

Product Status
■ In Production

Overview Resources Diagrams Ordering Support

This family of 2N1479 through 2N1482 medium-power, planar transistors is military qualified to the JAN level for high-reliability applications.

Package ESD Bag
 Carrier:

Electrical Rating	Symbol	Min	Typ	Max	Unit
DC Current Gain	HFE	35		100	
Turn Off Time (nS)	t _{off}			25000	ns

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector Current (dc)	I _C			1.5	A
Collector to Base Voltage (Emitter Open)	V _{CB0}			60	V
Collector to Emitter Saturation Voltage	V _{CE(sat)}			0.75	V
Collector-Emitter Voltage (Base Open)	V _{CEO}			40	V
Emitter-Base Voltage (Collector Open)	V _{EB0}			12	V
Junction Temperature (°C)	T _J	-65		200	°C
Power Dissipation	P _D			1	W
Thermal Resistance, Junction to Case (°C/W)	R _{θJC}			35	°C/W

Alphanumeric Parameter	Value
Quality Level	JAN

This part can be found in the following product categories:

- Power Discretets & Modules ▶ BJT (BiPolar Junction Transistor)
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